



Docket No.: M4065.0900/P900  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Patent Application of:  
Ramin Ghodsi

Application No.: 10/822,785

Confirmation No.: 3196

Filed: April 13, 2004

Art Unit: 2824

For: MULTI-CELL RESISTIVE MEMORY  
ARRAY ARCHITECTURE WITH SELECT  
TRANSISTOR

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Examiner: E. J. Wendler

**AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION**

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

**INTRODUCTORY COMMENTS**

In response to the Office Action dated January 10, 2006, please amend the above-identified U.S. patent application as follows:

**Amendments to the Drawings** are identified at page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 3 of this paper.

**Remarks** begin on page 12 of this paper.